Electrical Characteristics **(T_C=25 unless otherwise specified)**

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions	Note
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	1200	/	/	V	V_{GS}=0V, I_D=100μA	
$V_{GS(th)}$	Gate Threshold Voltage	2.0	2.8	4.0	V	V_{DS}=V_{GS}, I_D=20mA	Fig.11
		/	2.0	/		V_{DS}=V_{GS}, I_D=20mA, T_J=175	
I_{DSS}	Zero Gate Voltage Drain Current	/	1	100	μA	V_{DS}=1200V, V_{GS}=0V	
I_{GSS+}	Gate-Source Leakage Current	/	10	100	nA	V_{DS}=0V, V_{GS}=23V	
I_{GSS-}	Gate-Source Leakage Current	/	10	100	nA	V_{DS}=0V, V_{GS}=-10V	
$R_{DS(on)}$	Drain-Source On-State Resistance	/	20	27.4	mΩ	V_{GS}=18V, I_D=60A	Fig.
		/	30	/		V_{GS}=18V, I_D=60A, T_J=175	4,5,6

Figure 1. Output Characteristics T_J = -55 Ņ

Figure 2. Output Characteristics T_J = 25 Ņ

od91ed93.5 2d93. (e3)20.7 (8)-2.1 rd93.ree

Figure 3. Output Characteristics T_J = 175

Figure 4. Normalized On-Resistance vs. Temperature

Figure 5. On-Resistance vs. Daip Cuerrn

Typical Performance

8l)8Figure 76 (76 (76TEMCOTBB.963.248C Er)3 (n2)3 (an)5 32 8a10 (n)-2r)4.s oab- 9 (r9

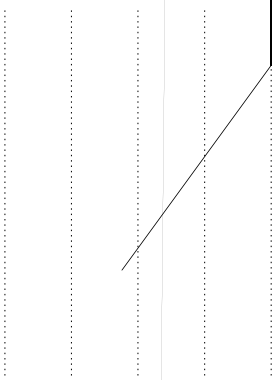

Figure 13. 3rd Quadrant Characteristic at -55

Figure 14. 3rd Quadrant Characteristic at 25

Figure 15. 3rd Quadrant Characteristic at 175

Figure 16. Output Capacitor Stored Energy

Figure 17. Capacitances vs. Drain-Source Voltage (0 - 200V)

Figure 18. Capacitances vs. Drain-Source Voltage (0 - 1200V)

Figure 19. Continuous Drain Current vs. Case Temperature

Figure 20. Maximum Power Dissipation vs. Case Temperature

21. DIP 67.4 w 12.6 (1 0.8 (

Figure 21. Continuous Drain Current vs.

Test Circuit Schematic

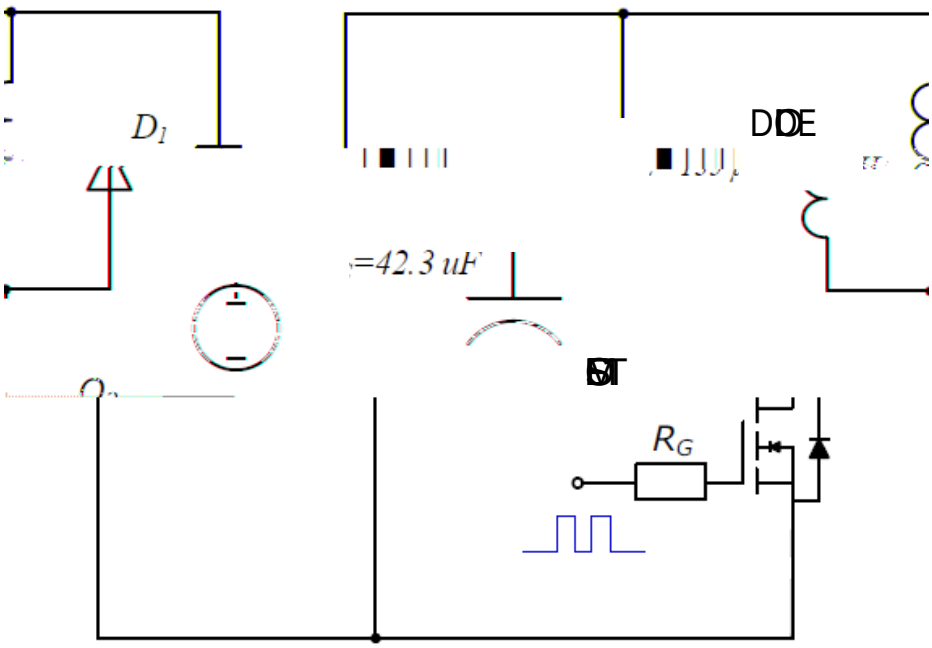

Figure 2 3. Clamped Inductive Switching Waveform Test Circuit

Notes

1) Before using our products, please [illegible]

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